

Product data sheet

1. General description

Ultrafast power diode in a SOD113 (2-lead TO-220F) plastic package.

2. Features and benefits

- Fast switching
- Isolated plastic package
- Low leakage current
- Low forward voltage drop
- Low thermal resistance
- Soft recovery characteristic
- Enhanced avalanche energy capability

3. Applications

- High frequency switched-mode power supplies
- Discontinuous Current Mode (DCM) Power Factor Correction (PFC)

4. Quick reference data

Table 1. Qui	ick reference data					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _{RRM}	repetitive peak reverse voltage		-	-	600	V
I _{F(AV)}	average forward current	δ = 0.5; T _h ≤ 71 °C; square-wave pulse; Fig. 1; Fig. 2; Fig. 3	-	-	10	A
Static charact	teristics	·			1	
V _F	forward voltage	I _F = 10 A; T _j = 150 °C; <u>Fig. 6</u>	-	-	1.6	V
Dynamic chai	racteristics	·				
t _{rr}	reverse recovery time	I _F = 1 A; V _R = 30 V; dI _F /dt = 50 A/μs; T _j = 25 °C; <u>Fig. 7</u>	-	35	50	ns
Avalanche en	ergy				1	,
E _{AS}	non-repetitive avalanche energy	I _R = 2.6 A; T _{j(init)} = 25 °C; L = 15 mH	-	50	-	mJ





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5. Pinning information

Table 2.	Pinning	information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	К	cathode	mb	K — A 001aaa020
2	А	anode		001aaa020
mb	n.c.	mounting base; isolated	TO-220F (SOD113)	

6. Ordering information

Table 3. Ordering in	formation		
Type number	Package		
	Name	Description	Version
BYV10EX-600P	TO-220F	plastic single-ended package; isolated heatsink mounted; 1 mounting hole; 2-lead TO-220 "full pack"	SOD113

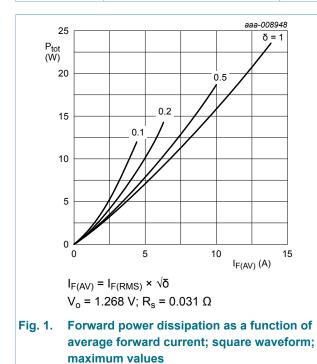
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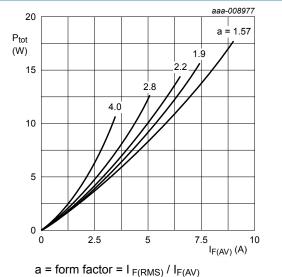
7. Limiting values

Table 4.Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V _{RRM}	repetitive peak reverse voltage		-	600	V
V _{RWM}	crest working reverse voltage		-	600	V
V _R	reverse voltage	DC	-	600	V
I _{F(AV)}	average forward current	δ = 0.5; T _h ≤ 71 °C; square-wave pulse; Fig. 1; Fig. 2; Fig. 3	-	10	A
I _{FRM}	repetitive peak forward current	δ = 0.5; t _p = 25 μs; T _h ≤ 71 °C; square- wave pulse	-	20	A
I _{FSM}	non-repetitive peak forward current	t_p = 10 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse; Fig. 4	-	75	A
		t_p = 8.3 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse; Fig. 4	-	83	A
T _{stg}	storage temperature		-65	175	°C
Tj	junction temperature		-	175	°C





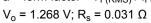


Fig. 2. Forward power dissipation as a function of average forward current; sinusoidal waveform; maximum values

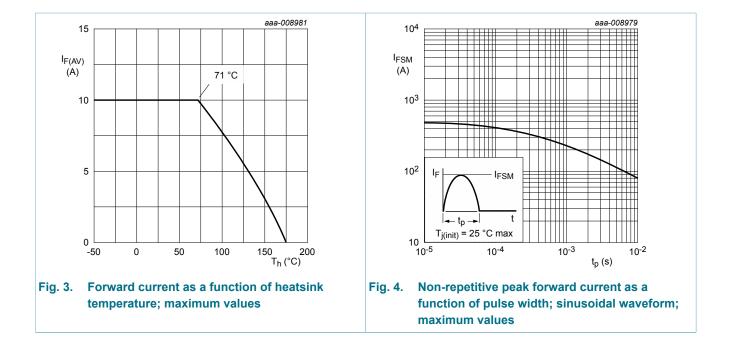
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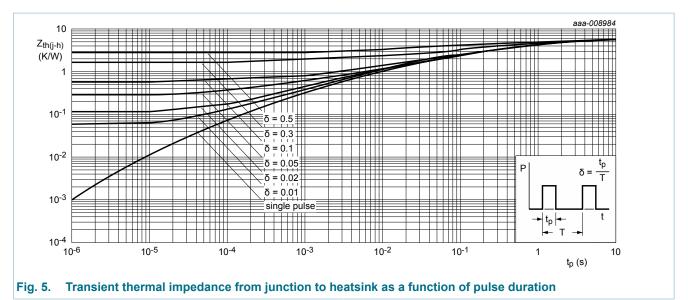
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8. Thermal characteristics

Table 5.	Thermal characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _{th(j-h)}	thermal resistance	without heatsink compound	-	-	7.2	K/W
	from junction to heatsink	with heatsink compound; Fig. 5	-	-	5.5	K/W
R _{th(j-a)}	thermal resistance from junction to ambient	in free air	-	55	-	K/W



9. Isolation characteristics

Table 6. Is	olation characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _{isol(RMS)}	RMS isolation voltage	50 Hz \leq f \leq 60 Hz; RH \leq 65 %; from all pins to external heatsink; sinusoidal waveform; clean and dust free	-	-	2500	V
C _{isol}	isolation capacitance	f = 1 MHz; from cathode to external heatsink	-	10	-	pF

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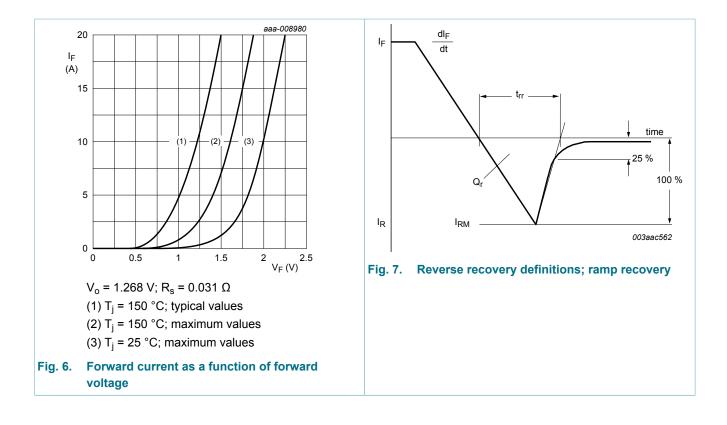
10. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	acteristics		Ċ	·		
V _F	forward voltage	I _F = 10 A; T _j = 25 °C; <u>Fig. 6</u>	-	1.55	2	V
		I _F = 10 A; T _j = 150 °C; <u>Fig. 6</u>	-	-	1.6	V
I _R	reverse current	V _R = 600 V; T _j = 25 °C	-	-	10	μA
		V _R = 500 V; T _j = 150 °C	-	-	250	μA
Dynamic cł	naracteristics	· · · · · · · · · · · · · · · · · · ·	I			
Qr	recovered charge	I _F = 10 A; V _R = 200 V; dI _F /dt = 200 A/ μs; T _j = 25 °C; <u>Fig. 7</u>	-	123	-	nC
		I_F = 10 A; V _R = 200 V; dI _F /dt = 200 A/ µs; T _j = 125 °C; <u>Fig. 7</u>	-	305	-	nC
t _{rr}	reverse recovery time	I_F = 1 A; V_R = 30 V; dI_F/dt = 50 A/µs; T _j = 25 °C; Fig. 7	-	35	50	ns
		I_F = 10 A; V _R = 200 V; dI _F /dt = 200 A/ µs; T _j = 25 °C; <u>Fig. 7</u>	-	50	-	ns
		I_F = 10 A; V _R = 200 V; dI _F /dt = 200 A/ µs; T _j = 125 °C; <u>Fig. 7</u>	-	78	-	ns
		I _F = 10 A; V _R = 400 V; dI _F /dt = 500 A/ μs; T _j = 25 °C; <u>Fig. 7</u>	-	42	-	ns
I _{RM}	peak reverse recovery current	I _F = 10 A; V _R = 200 V; dI _F /dt = 200 A/ μs; T _j = 25 °C; <u>Fig. 7</u>	-	4.9	-	A
		I _F = 10 A; V _R = 200 V; dI _F /dt = 200 A/ μs; T _j = 125 °C; <u>Fig. 7</u>	-	7.8	-	A
Avalanche	energy	· · · · · · · · · · · · · · · · · · ·	1	1		
E _{AS}	non-repetitive avalanche energy	I _R = 2.6 A; T _{j(init)} = 25 °C; L = 15 mH	-	50	-	mJ

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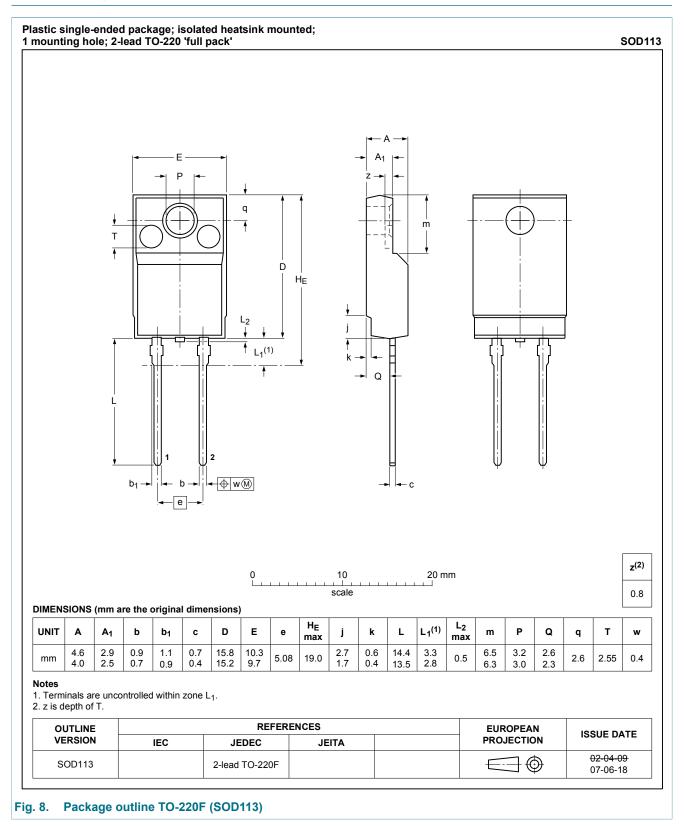
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11. Package outline



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12. Legal information

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Document status [1][2]	Product status [<u>3]</u>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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